

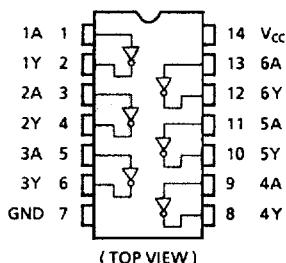
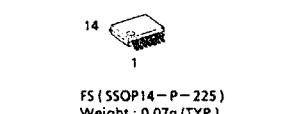
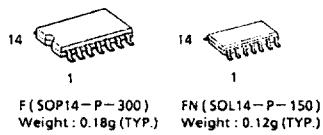
### HEX Inverter

The TC74LVQ04 is a high speed CMOS HEX INVERTER fabricated with silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

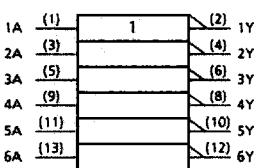
Designed for use in 3.3 Volt systems, it achieves high speed operation while maintaining the CMOS low power dissipation. The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

### Features

- High Speed:  $t_{pd} = 4.1\text{ ns}$  (Typ.) at  $V_{CC} = 3.3\text{ V}$
- Low Power Dissipation:  $I_{CC} = 2.5\mu\text{A}$  (Max.) at  $T_a = 25^\circ\text{C}$
- Input Voltage Level:
  - $V_{IL} = 0.8\text{ V}$  (Max.) at  $V_{CC} = 3\text{ V}$
  - $V_{IH} = 2.0\text{ V}$  (Min.) at  $V_{CC} = 3\text{ V}$
- Symmetrical Output Impedance:  $I_{OHL} = I_{OL} = 12\text{ mA}$  (Min.)
- Balanced Propagation Delays:  $t_{PLH} \approx t_{PHL}$
- Pin and Function Compatible with 74HC04



Pin Assignment



IEC Logic Symbol

Truth Table

Inputs	Outputs
A	Y
L	H
H	L

**Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Supply Voltage Range	V <sub>CC</sub>	-0.5 ~ 7.0	V
DC Input Voltage	V <sub>IN</sub>	-0.5 ~ V <sub>CC</sub> + 0.5	V
DC Output Voltage	V <sub>OUT</sub>	-0.5 ~ V <sub>CC</sub> + 0.5	V
Input Diode Current	I <sub>IK</sub>	±20	mA
Output Diode Current	I <sub>OK</sub>	±50	mA
DC Output Current	I <sub>OUT</sub>	±50	mA
DC V <sub>CC</sub> /Ground Current	I <sub>CC</sub>	±150	mA
Power Dissipation	P <sub>D</sub>	180	mW
Storage Temperature	T <sub>STG</sub>	-65 ~ 150	°C
Lead Temperature 10sec	T <sub>L</sub>	300	°C

**Recommended Operating Conditions**

Parameter	Symbol	Value	Unit
Supply Voltage	V <sub>CC</sub>	2.0 ~ 3.6	V
Input Voltage	V <sub>IN</sub>	0 ~ V <sub>CC</sub>	V
Output Voltage	V <sub>OUT</sub>	0 ~ V <sub>CC</sub>	V
Operating Temperature	T <sub>OPR</sub>	-40 ~ 85	°C
Input Rise and Fall Time	dI/dV	0 ~ 100	ns/V

**DC Electrical Characteristics**

Parameter	Symbol	Test Condition	V <sub>CC</sub> (V)	Ta = 25°C			Ta = -40 ~ 85°C		Unit
				Min.	Typ.	Max.	Min.	Max.	
High-Level Input Voltage	V <sub>IH</sub>	—	3.0	2.0	—	—	2.0	—	V
Low-Level Input Voltage	V <sub>IL</sub>	—	3.0	—	—	0.8	—	0.8	
High-Level Output Voltage	V <sub>OH</sub>	V <sub>IN</sub> = V <sub>IL</sub> I <sub>OH</sub> = -50µA I <sub>OH</sub> = -12mA	3.0 3.0	2.9 2.58	3.0	—	2.9 2.48	—	
Low-Level Output Voltage	V <sub>OL</sub>	V <sub>IN</sub> = V <sub>IH</sub> I <sub>OL</sub> = 50µA I <sub>OL</sub> = 12mA	3.0 3.0	—	0.0	0.1	—	0.1	
Input Leakage Current	I <sub>IN</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND	3.6	—	—	±0.1	—	±1.0	
Quiescent Supply Current	I <sub>CC</sub>	V <sub>IN</sub> = V <sub>CC</sub> or GND	3.6	—	—	2.5	—	25.0	µA

**AC Electrical Characteristics (Input  $t_i = t_r = 3\text{ns}$ ,  $C_L = 50\text{pF}$ ,  $R_L = 500\Omega$ )**

Parameter	Symbol	Test Condition	$V_{CC}$ (V)	Ta = 25°C			Ta = -40 ~ 85°C		Unit
				Min	Typ.	Max.	Min.	Max.	
Propagation Delay Time	$t_{PLH}$ $t_{PHL}$	(Note 1)	2.7 3.3±0.3	—	6.0 5.0	12.7 9.0	1.0 1.0	15.0 10.0	ns
Output to Output Skew	$t_{osLH}$ $t_{osHL}$		2.7 3.3±0.3	—	—	1.5 1.5	—	1.5 1.5	
Input Capacitance	$C_{IN}$	(Note 2)		—	5	10	—	10	pF
Power Dissipation Capacitance	$C_{PD}$	(Note 3)		—	20	—	—	—	

Note (1) Parameter guaranteed by design.  $t_{osLH} = |t_{PLHm} - t_{PLHn}|$ ,  $t_{osHL} = |t_{PHLm} - t_{PHLn}|$ 

Note (2) Parameter guaranteed by design.

Note (3)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption.

Average operating current can be obtained by the equation:

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per Gate)}$$

**Noise Characteristics (Input  $t_i = t_r = 3\text{ns}$ ,  $C_L = 50\text{pF}$ ,  $R_L = 500\Omega$ )**

Parameter	Symbol	Test Condition	$V_{CC}$	Ta = 25°C			Unit
				Typ.	Max.		
Quiet Output Maximum Dynamic $V_{OL}$	$V_{OLD}$		3.3	0.5	0.8		V
Quiet Output Minimum Dynamic $V_{OL}$	$V_{OLV}$		3.3	-0.5	-0.8		V
Minimum High Level Dynamic Input Voltage	$V_{IHd}$		3.3	—	2.0		V
Maximum Low Level Dynamic Input Voltage	$V_{ILd}$		3.3	—	0.8		V

**Notes**

1. This technical data may be controlled under U.S. Export Administration Regulations and may be subject to the approval of the U.S. Department of Commerce prior to export. Any export or re-export, directly or indirectly, in contravention of the U.S. Export Administration Regulations is strictly prohibited.
2. **LIFE SUPPORT POLICY**  
Toshiba products described in this document are not authorized for use as critical components in life support systems without the written consent of the appropriate officer of Toshiba America, Inc. Life support systems are either systems intended for surgical implant in the body or systems which sustain life.  
A critical component in any component of a life support system whose failure to perform may cause a malfunction of the life support system, or may affect its safety or effectiveness.
3. The information in this document has been carefully checked and is believed to be reliable; however no responsibility can be assumed for inaccuracies that may not have been caught. All information in this data book is subject to change without prior notice. Furthermore, Toshiba cannot assume responsibility for the use of any license under the patent rights of Toshiba or any third parties.